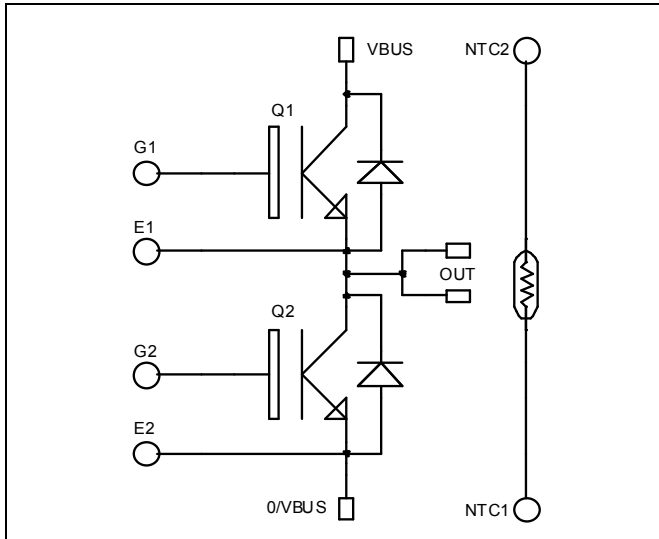


*Phase leg  
Trench + Field Stop IGBT  
Power Module*

**$V_{CES} = 600V$   
 $I_C = 300A @ T_c = 80^\circ C$**

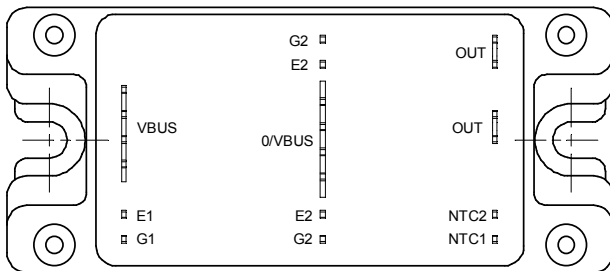


### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

### Features

- Trench + Field Stop IGBT Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring



### Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive  $T_C$  of  $V_{CEsat}$
- Low profile
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	600	V
$I_C$	Continuous Collector Current	$T_C = 25^\circ C$	430
		$T_C = 80^\circ C$	300
$I_{CM}$	Pulsed Collector Current	$T_C = 25^\circ C$	450
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_C = 25^\circ C$	935
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$	600A @ 550V



**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$			350	$\mu\text{A}$
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 300A$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	1.5 1.7	1.9	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.5\text{ mA}$	5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			500	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0V$		18.4		nF
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$		1.16		
$C_{res}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		0.54		
$Q_G$	Gate charge	$V_{GE} = \pm 15V, I_C = 300A$ $V_{CE} = 300V$		3.2		$\mu\text{C}$
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 300A$ $R_G = 2.2\Omega$		115		ns
$T_r$	Rise Time			45		
$T_{d(off)}$	Turn-off Delay Time			225		
$T_f$	Fall Time			55		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $150^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 300A$ $R_G = 2.2\Omega$		130		ns
$T_r$	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			300		
$T_f$	Fall Time			70		
$E_{on}$	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	1.7 3		mJ
$E_{off}$	Turn off Energy	$I_C = 300A$ $R_G = 2.2\Omega$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	8.2 10.6		mJ
$I_{sc}$	Short Circuit data	$V_{GE} \leq 15V; V_{Bus} = 360V$ $t_p \leq 6\mu\text{s}; T_j = 150^\circ\text{C}$		1500		A

**Reverse diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		600			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 600V$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$		150 400	$\mu\text{A}$
$I_F$	DC Forward Current		$T_c = 80^\circ\text{C}$	300		A
$V_F$	Diode Forward Voltage	$I_F = 300A$ $V_{GE} = 0V$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	1.6 1.5	2	V
$t_{rr}$	Reverse Recovery Time	$I_F = 300A$ $V_R = 300V$ $di/dt = 4000A/\mu\text{s}$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	130 225		ns
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	13.7 29		$\mu\text{C}$
$E_r$	Reverse Recovery Energy		$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	3.2 7		mJ

**Temperature sensor NTC** (see application note APT0406 on [www.microsemi.com](http://www.microsemi.com) for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
ΔR <sub>25</sub> /R <sub>25</sub>			5		%
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K
ΔB/B	T <sub>C</sub> = 100°C		4		%

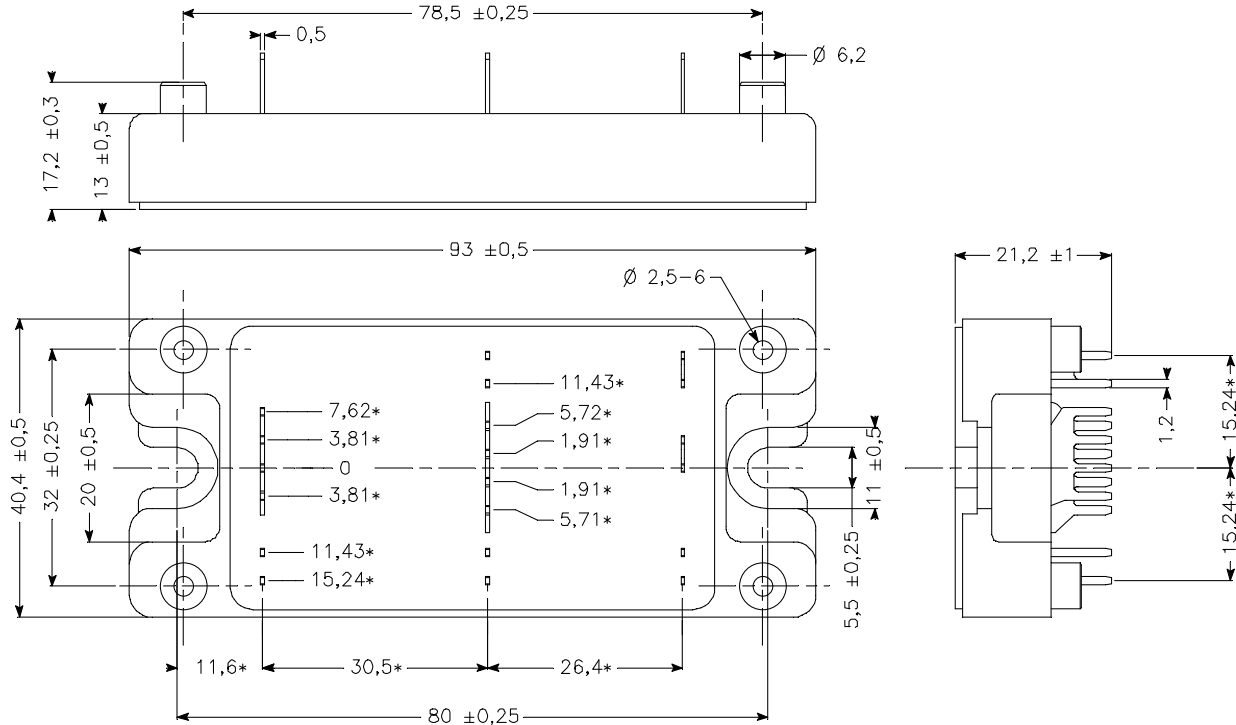
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

## Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R <sub>thJC</sub>	Junction to Case Thermal Resistance	IGBT		0.16	°C/W	
		Diode		0.29		
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t = 1 min, I <sub>isol</sub> < 1mA, 50/60Hz	2500			V	
T <sub>J</sub>	Operating junction temperature range	-40		175	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		100		
Torque	Mounting torque	To Heatsink	M5	2.5	4.7	N.m
Wt	Package Weight				160	g

## SP4 Package outline (dimensions in mm)

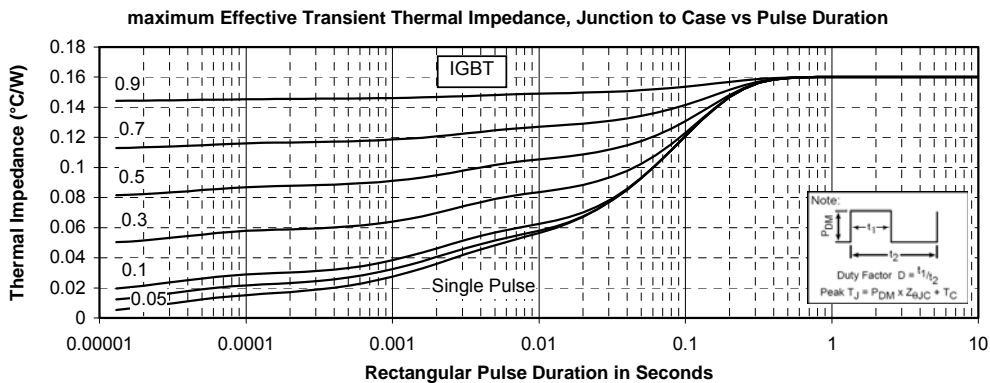
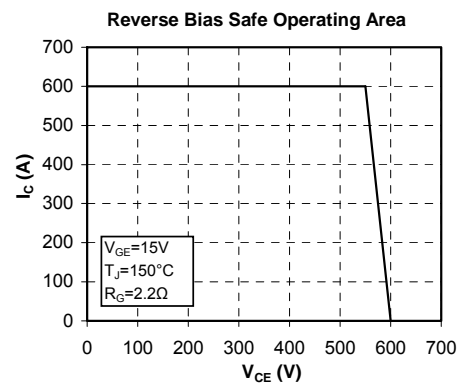
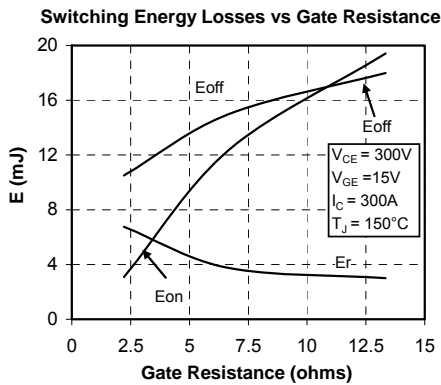
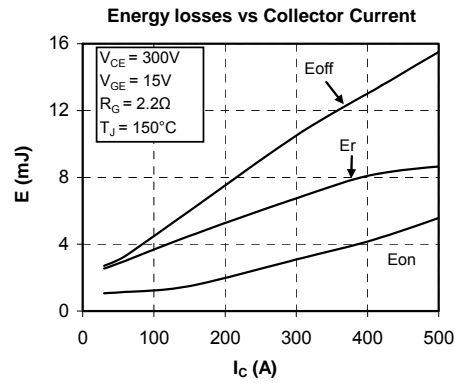
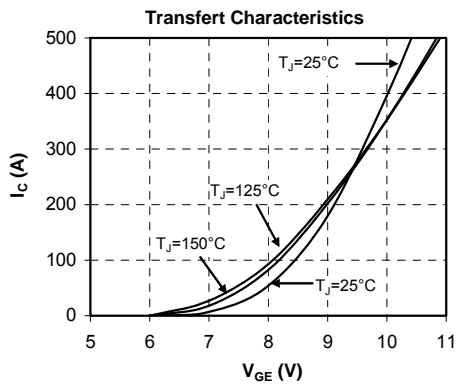
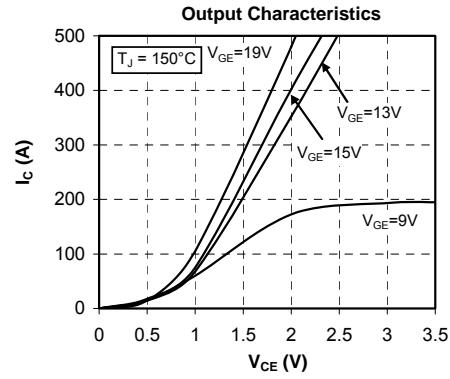
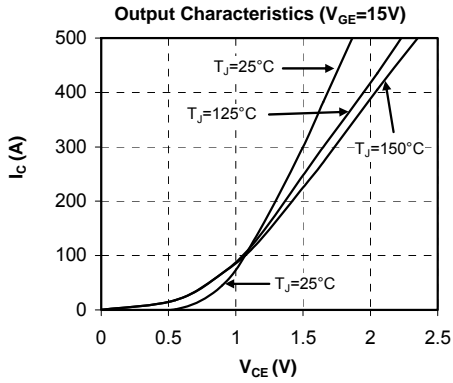


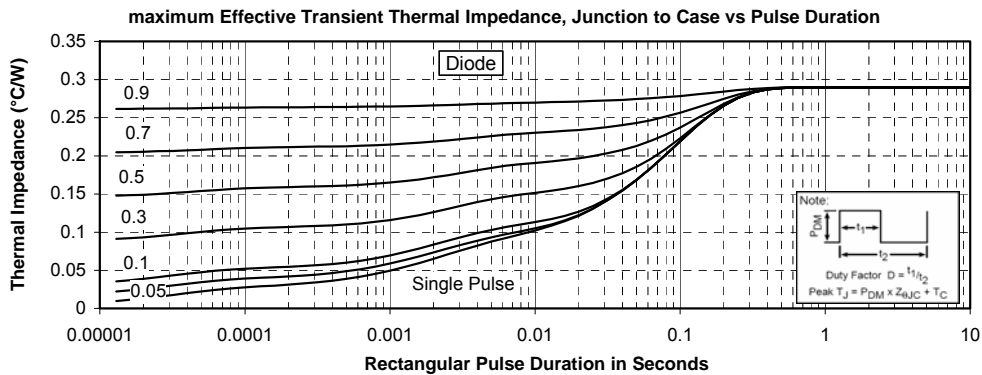
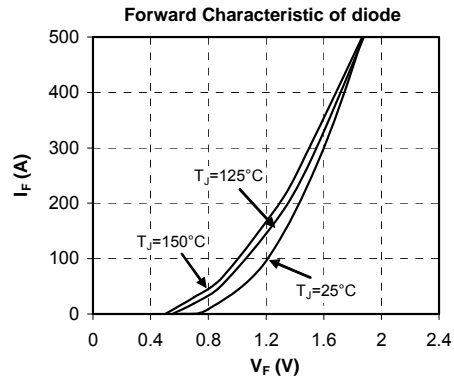
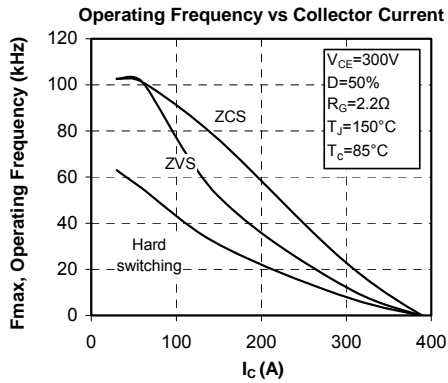
ALL DIMENSIONS MARKED "\*" ARE TOLERENCED AS:  $\pm 0,1$

application note APT0501 - Mounting Instructions for SP4 Power Modules on [www.microsemi.com](http://www.microsemi.com)

See

## Typical Performance Curve





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